

Amendments

In the Claims:

Please cancel claim 6; amend claims 1 and 7-13 as follows:

Sub 1
1. A wiring layer structure connected to a first electrode of a ferroelectric capacitor having first and second electrodes, comprising:

a main wiring layer including a first material that reacts with a substance to produce a reducing agent, said substance being infiltrated from the outside to this main wiring layer; and

a coating layer including a first coating part provided between said main wiring layer and said first electrode, a second coating part provided on the top surface of said main wiring layer, and a third coating part provided on side faces of said main wiring layer;

wherein said coating layer is conductive and comprises a second material for preventing the infiltration of said substance into said main wiring layer.

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7. The wiring layer structure according to Claim 1, wherein said first, second, and third coating parts are titanium nitride (TiN) films.

8. The wiring layer structure according to Claim 1, wherein said first and third coating parts are titanium nitride (TiN) films, and said second coating part is a built-up film composed of a titanium (Ti) film and a titanium nitride (TiN) film.

9. The wiring layer structure according to Claim 1, wherein said first coating part is a titanium nitride (TiN) film, and wherein said second and third coating parts are built-up films composed of a titanium (Ti) film and a titanium nitride (TiN) film.

10. The wiring layer structure according to Claim 1, wherein said first coating part is a titanium nitride (TiN) sputtering film, and said second and third coating parts are TiN-CVD films.